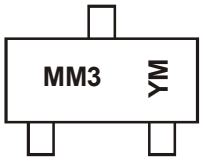
Marking Information



MM3 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: I = 2021)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2011	……	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Y	……	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	300 230	mA
Continuous Drain Current (Note 6) V_{GS} = 5V	Steady State	T_A = +25°C T_A = +70°C	I_D	260 210	mA
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	800	mA
Maximum Body Diode Continuous Current (Note 6)			I_S	300	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	300	mW
	(Note 6)		432	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	398	°C/W
	(Note 6)		290	
Thermal Resistance, Junction to Case	(Note 5)	$R_{\theta JC}$	142	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	V_{DS} = 60V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±5.0	μA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1.2	—	2.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	2	3	Ω	V_{GS} = 10V, I_D = 0.115A
		—	2.5	4	Ω	V_{GS} = 5V, I_D = 0.115A
Forward Transconductance	g_{FS}	80	290	—	mS	V_{DS} = 10V, I_D = 0.115A
Diode Forward Voltage	V_{SD}	-	0.8	1.2	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	22.0	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	3.2	—		
Reverse Transfer Capacitance	C_{rss}	—	2.0	—		
Gate Resistance	R_G	—	79.9	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge V_{GS} = 10V	Q_g	—	0.87	—	nC	V_{GS} = 10V, V_{DS} = 30V, I_D = 150mA
Total Gate Charge V_{GS} = 4.5V	Q_g	—	0.43	—		
Gate-Source Charge	Q_{gs}	—	0.11	—		
Gate-Drain Charge	Q_{gd}	—	0.11	—		
Turn-On Delay Time	$t_{D(on)}$	—	2.7	—	nS	V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V, R_{GEN} = 25Ω
Turn-On Rise Time	t_r	—	2.8	—		
Turn-Off Delay Time	$t_{D(off)}$	—	12.6	—		
Turn-Off Fall Time	t_f	—	7.3	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

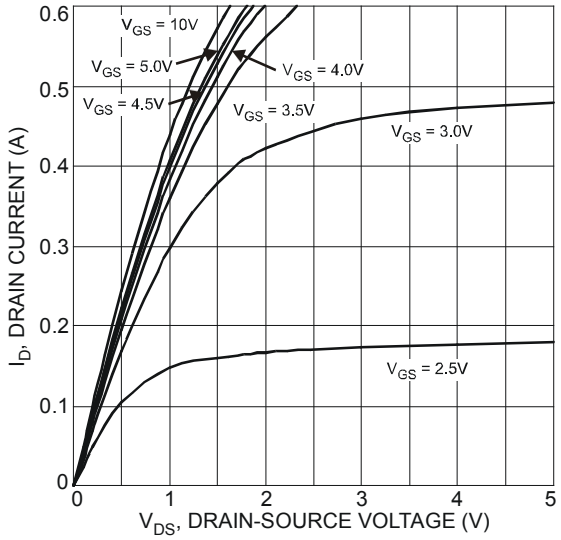


Figure 1 Typical Output Characteristic

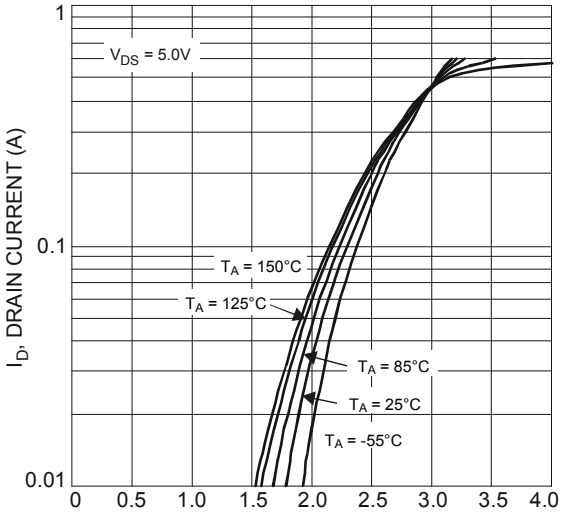


Figure 2 Typical Transfer Characteristics

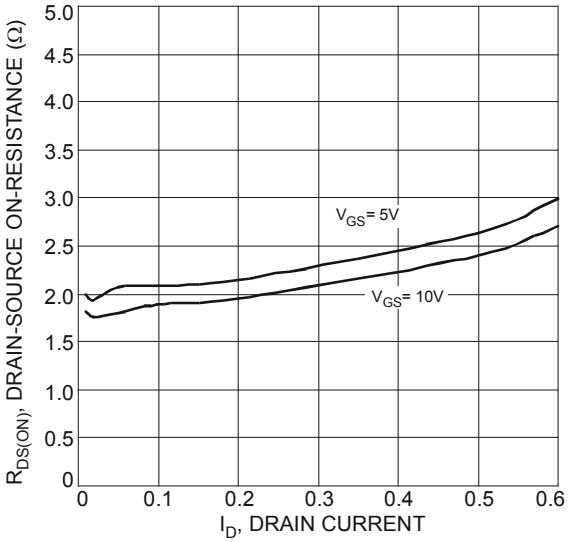


Figure 3 Typical On-Resistance vs. Drain Current and Temperature

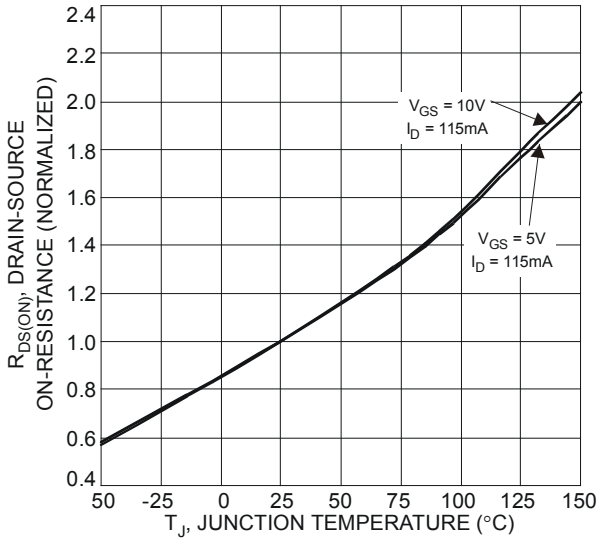


Figure 4 On-Resistance Variation with Temperature

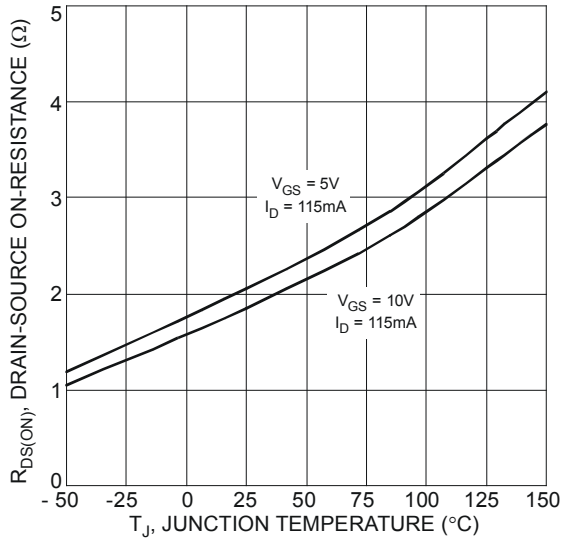


Figure 5 On-Resistance Variation with Temperature

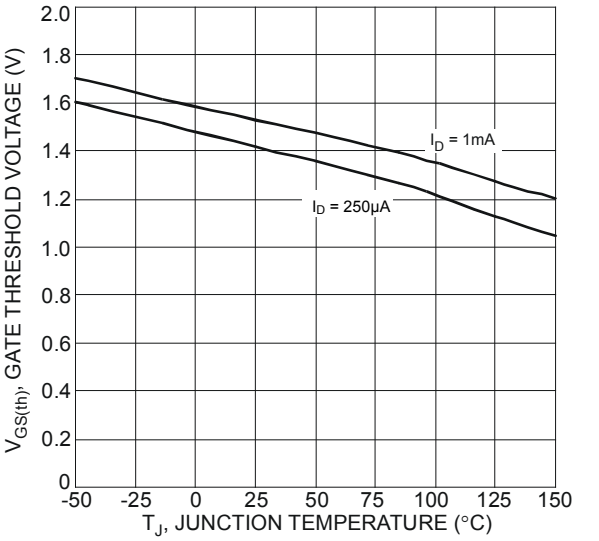


Figure 6 Gate Threshold Variation vs. Ambient Temperature

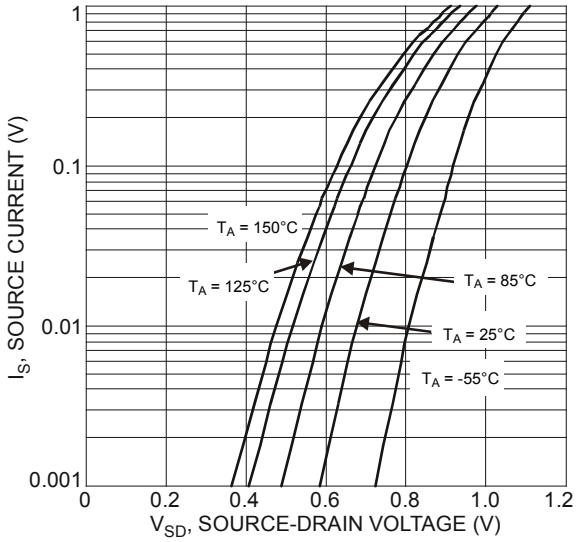


Figure 7 Diode Forward Voltage vs. Current

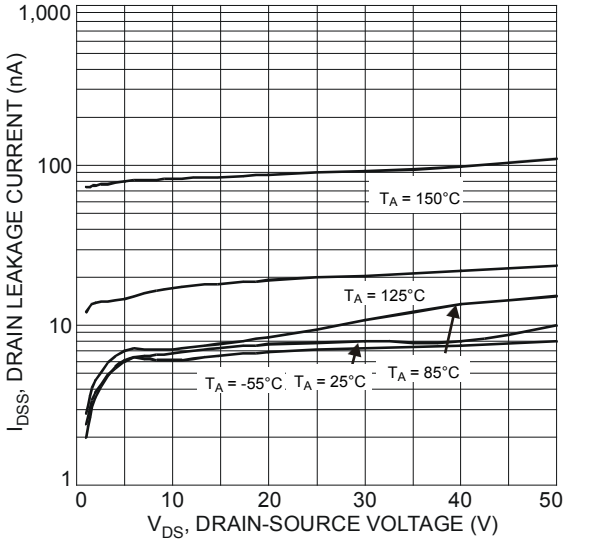


Figure 8 Typical Drain-Source Leakage Current vs. Voltage

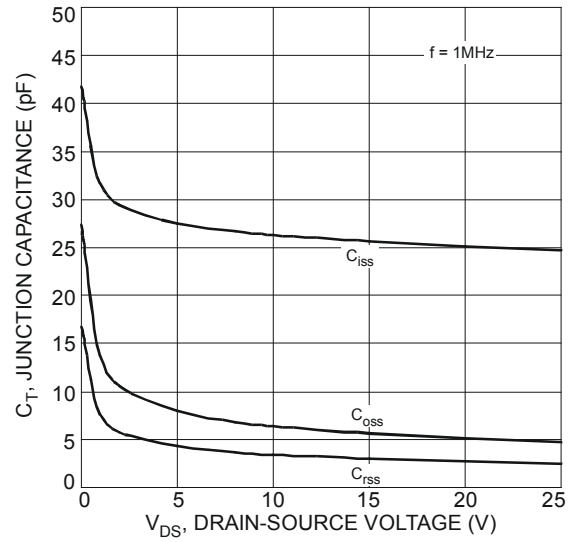


Figure 9 Typical Junction Capacitance

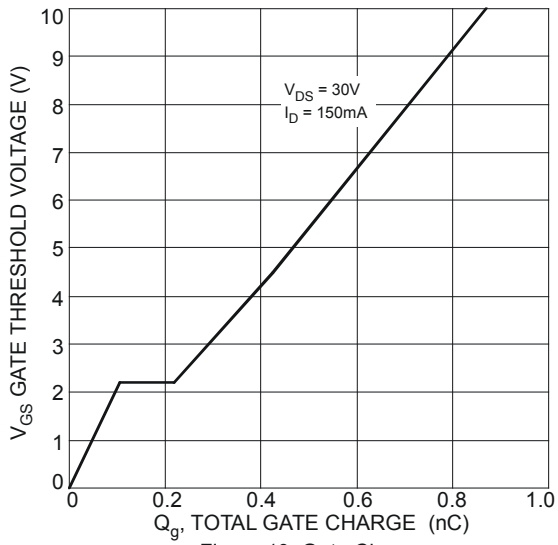
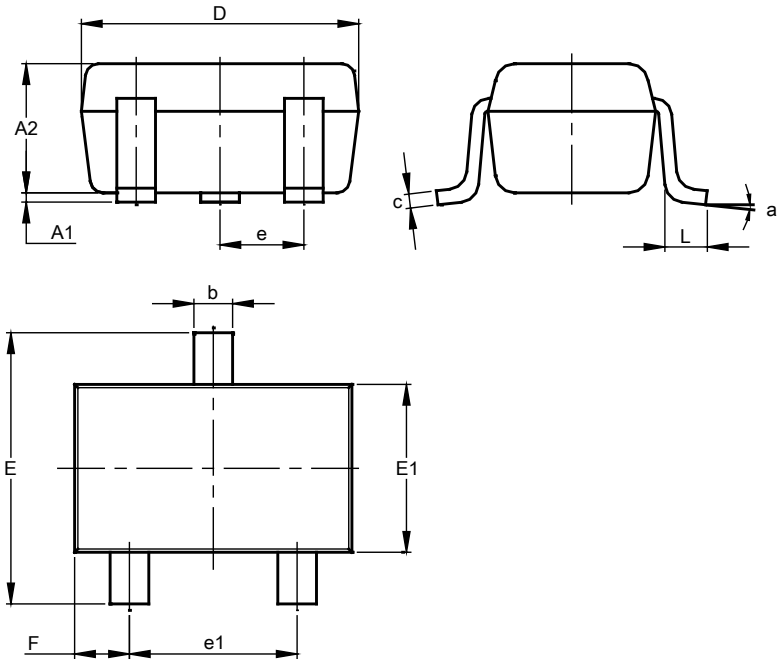


Figure 10 Gate Charge

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323 (Standard)

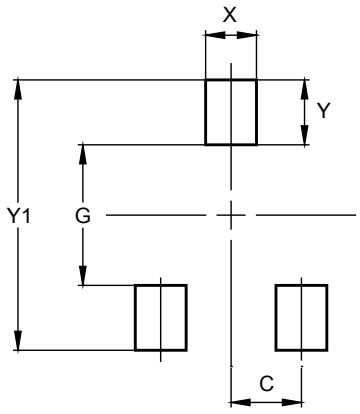


SOT323 (Standard)			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.20	0.40	0.30
c	0.08	0.18	0.13
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
e1	1.20	1.40	1.30
F	0.25	0.475	0.3625
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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